

Stud Thyristor

Line Thyristor

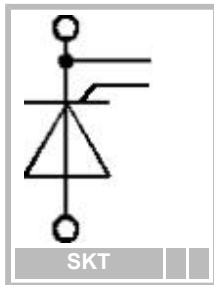
SKT 250

Features

- Hermetic metal case with glass insulator
- Threaded stud ISO M24x1,5
- High i_{2t} and I_{TSM} values for easy fusing
- International standard case

Typical Applications

- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers (e. g. for temperature control)
- Recommended snubber network e. g. for $V_{VRMS} \leq 400$ V:
 $R = 33 \cdot /32$ W, $C = 0,47 \cdot F$



V_{RSM}	V_{RRM}, V_{DRM}	$I_{TRMS} = 450$ A (maximum value for continuous operation)
V	V	$I_{TAV} = 250$ A (sin. 180; $T_c = 85$ °C)
500	400	SKT 250/04D
900	800	SKT 250/08D
1300	1200	SKT 250/12E
1500	1400	SKT 250/14E
1700	1600	SKT 250/16E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 100$ (85) °C	185 (250)	A
I_D	K0,55; $T_a = 45$ °C; B2 / B6	240 / 330	A
	K0,55F; $T_a = 35$ °C; B2 / B5	490 / 675	A
I_{RMS}	K0,55; $T_a = 45$ °C; W1C	265	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms	7000	A
	$T_{vj} = 130$ °C; 10 ms	6000	A
i_{2t}	$T_{vj} = 25$ °C; 8,35 ... 10 ms	245000	A ² s
	$T_{vj} = 130$ °C; 8,35 ... 10 ms	180000	A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 800$ A	max. 1,65	V
$V_{T(TO)}$	$T_{vj} = 130$ °C	max. 1	V
r_T	$T_{vj} = 130$ °C	max. 0,7	m•
$I_{DD}; I_{RD}$	$T_{vj} = 130$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 50	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/ μ s	1	μ s
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μ s
$(di/dt)_{cr}$	$T_{vj} = 130$ °C	max. 100	A/ μ s
$(dv/dt)_{cr}$	$T_{vj} = 130$ °C; SKT ...D / SKT ...E	max. 500 / 1000	V/ μ s
t_q	$T_{vj} = 130$ °C	50 ... 150	μ s
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 250	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33 \cdot$; typ. / max.	300 / 600	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 3	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 200	mA
V_{GD}	$T_{vj} = 130$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 130$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.	0,11	K/W
$R_{th(j-c)}$	sin. 180	0,123	K/W
$R_{th(j-c)}$	rec. 120	0,137	K/W
$R_{th(c-s)}$		0,015	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 55 ... + 150	°C
V_{isol}		-	V~
M_s	to heatsink	60	Nm
a		5 * 9,81	m/s ²
m	approx.	490	g
Case		B 7	

Diagrams

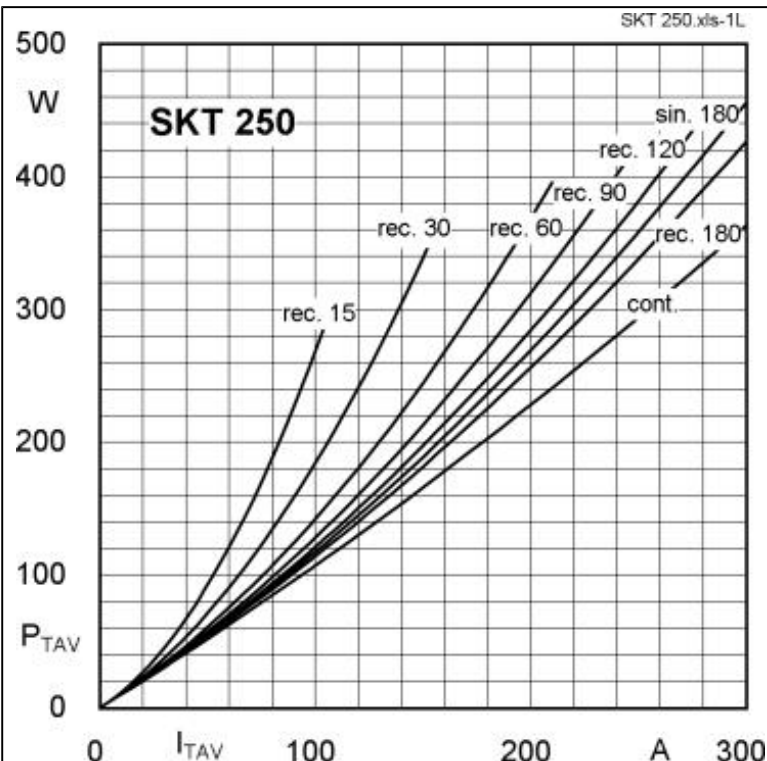


Fig. 1L Power dissipation vs. on-state current

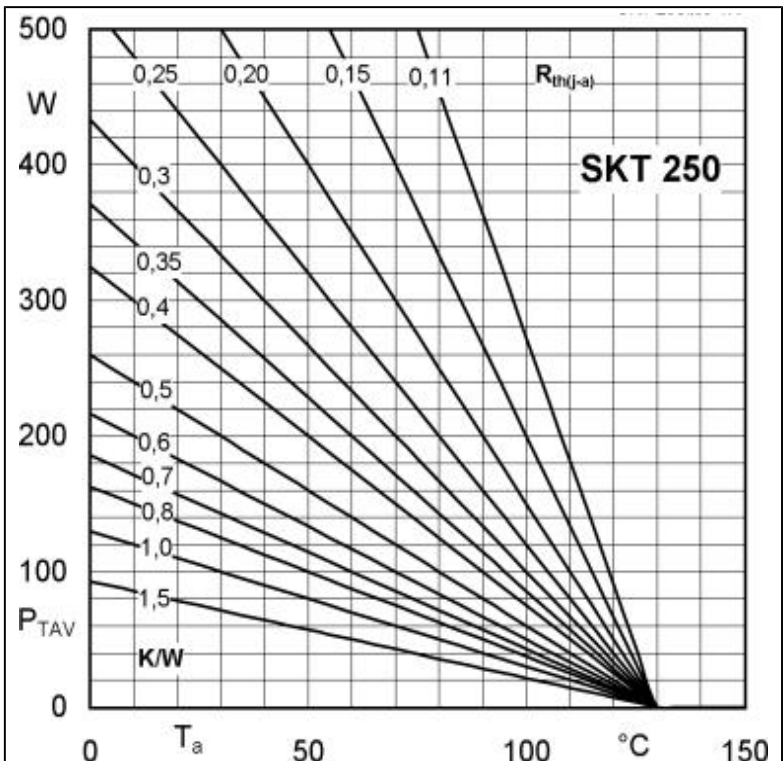


Fig. 1R Power dissipation vs. ambient temperature

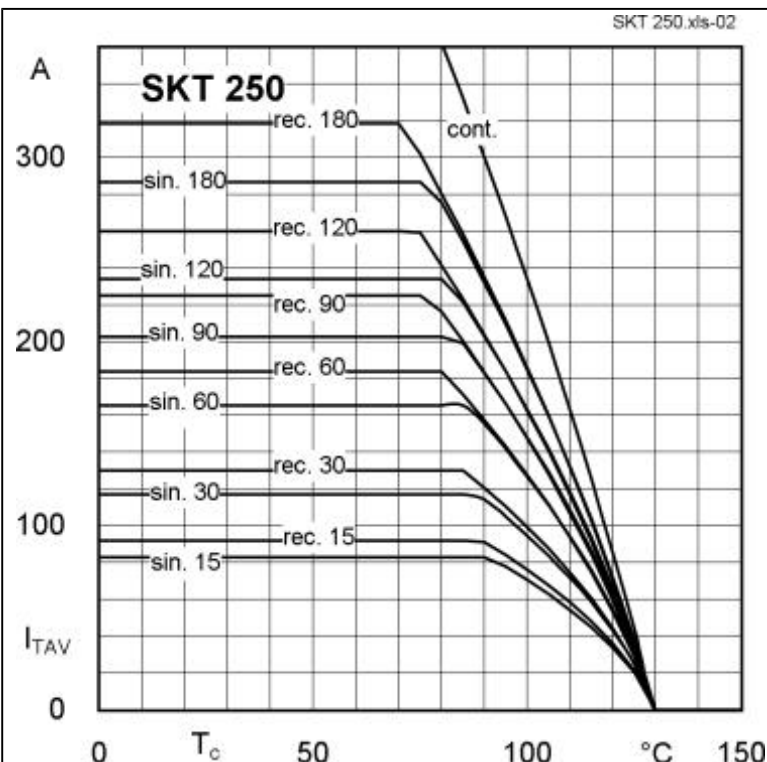


Fig. 2 Rated on-state current vs. case temperature

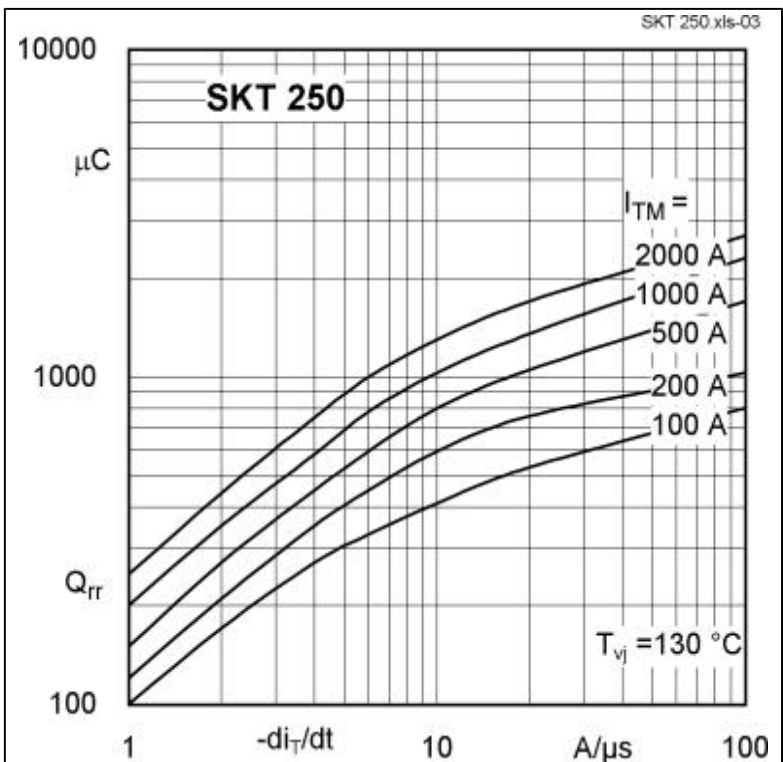


Fig. 3 Recovered charge vs. current decrease

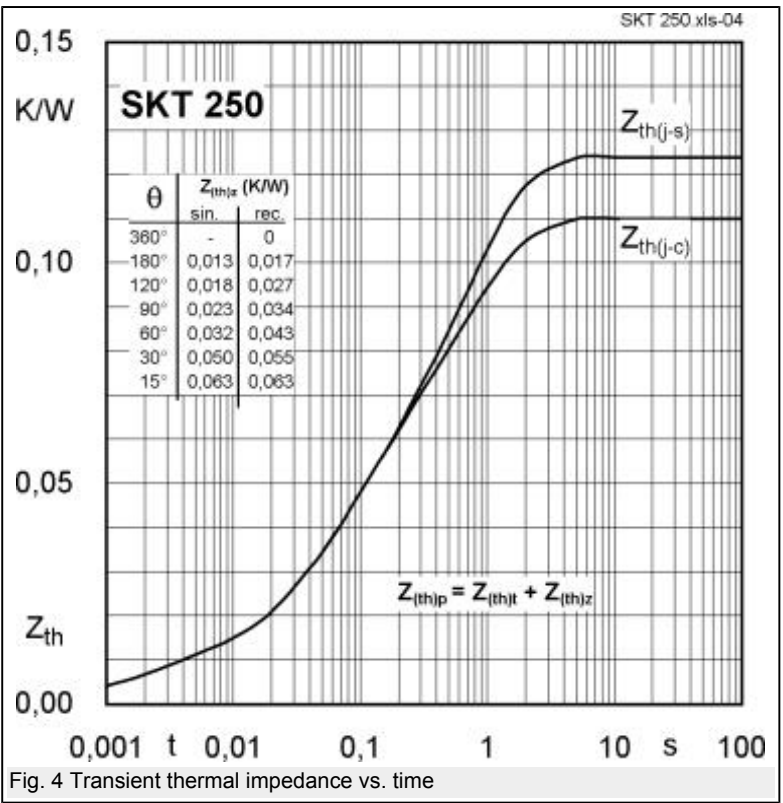


Fig. 4 Transient thermal impedance vs. time

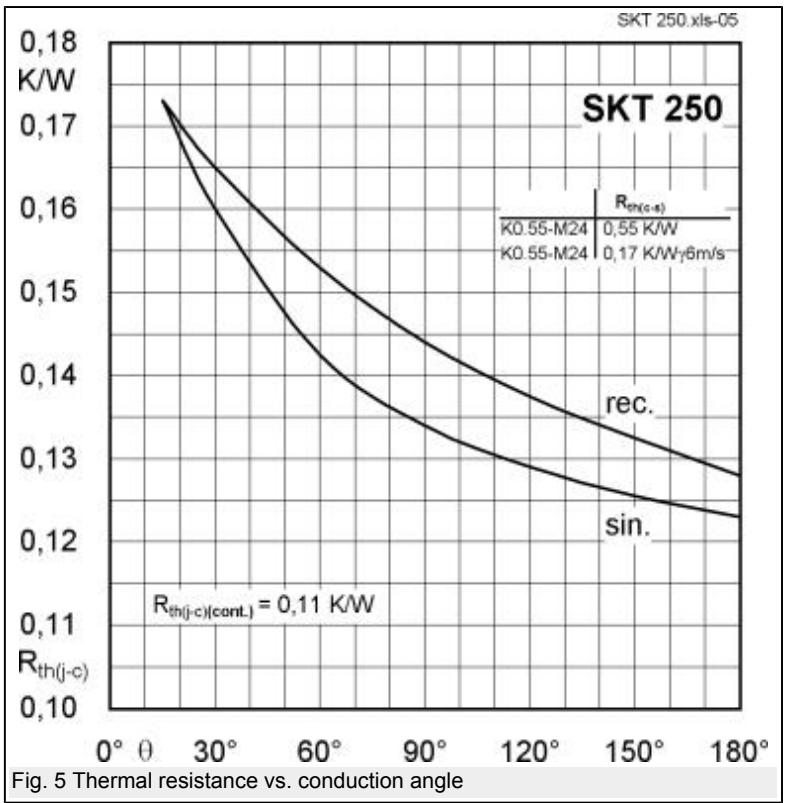


Fig. 5 Thermal resistance vs. conduction angle

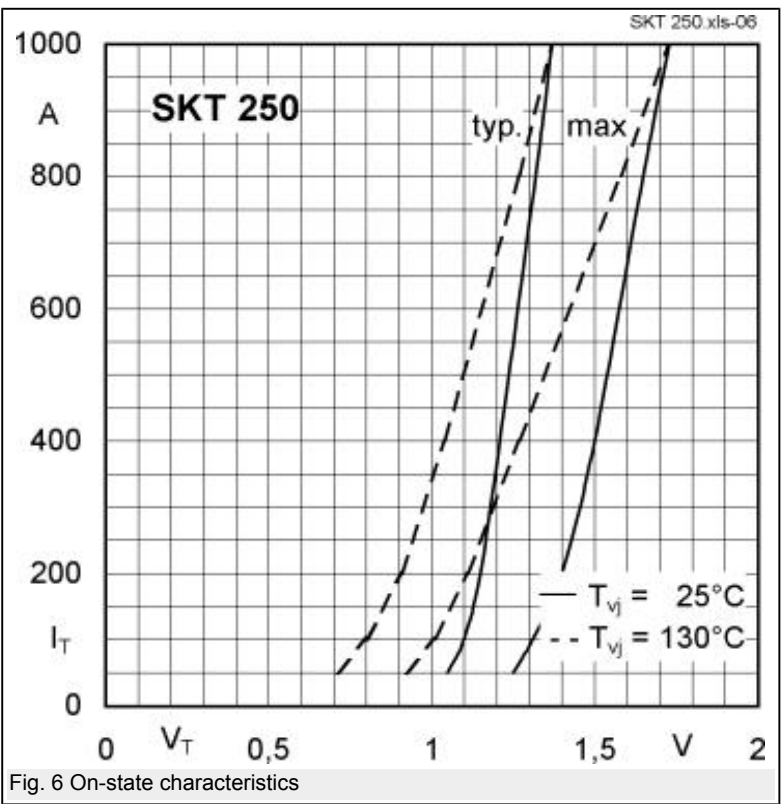


Fig. 6 On-state characteristics

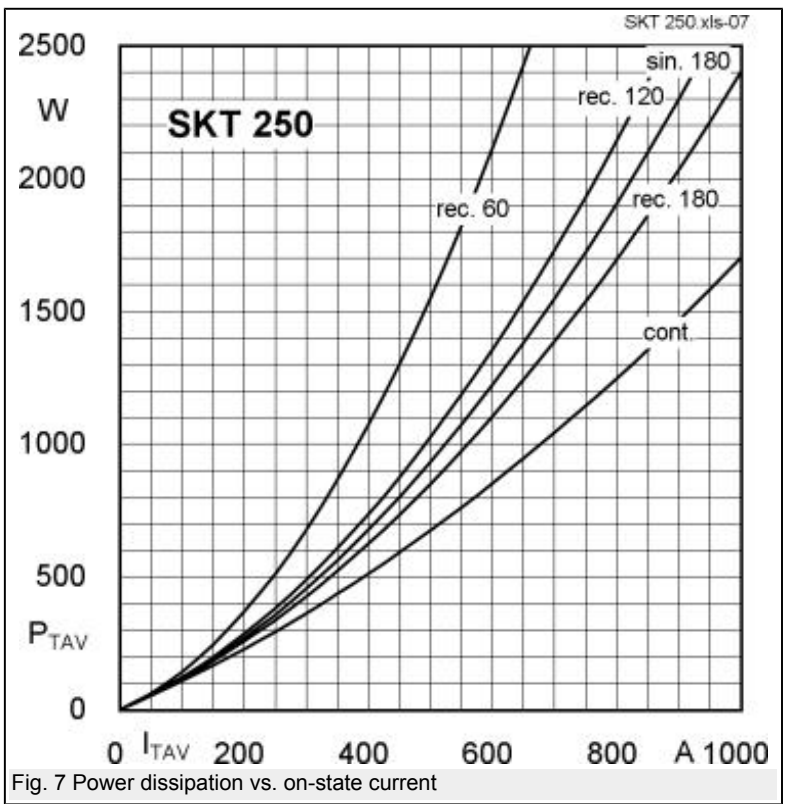


Fig. 7 Power dissipation vs. on-state current

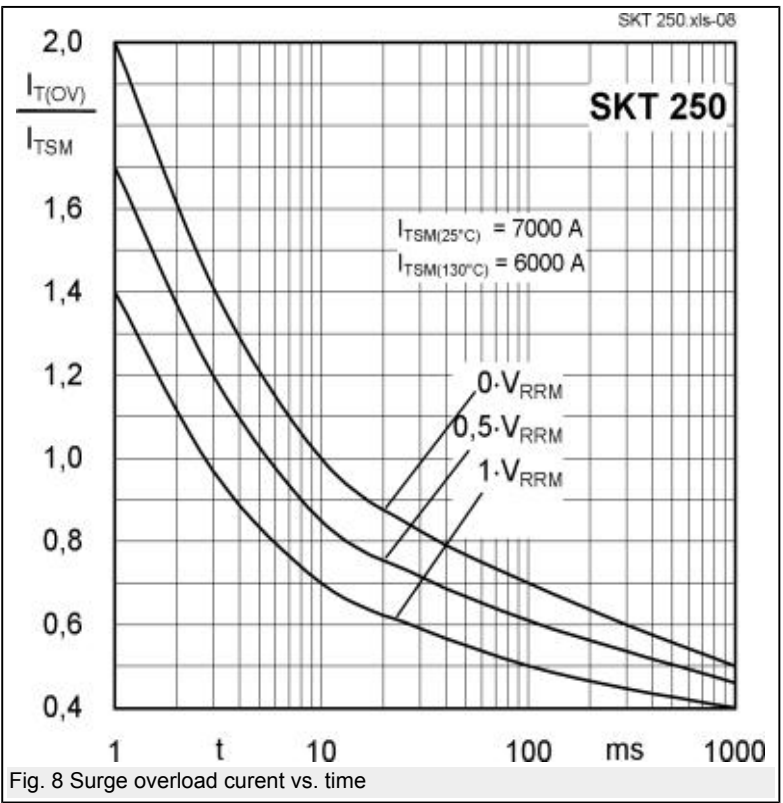


Fig. 8 Surge overload current vs. time

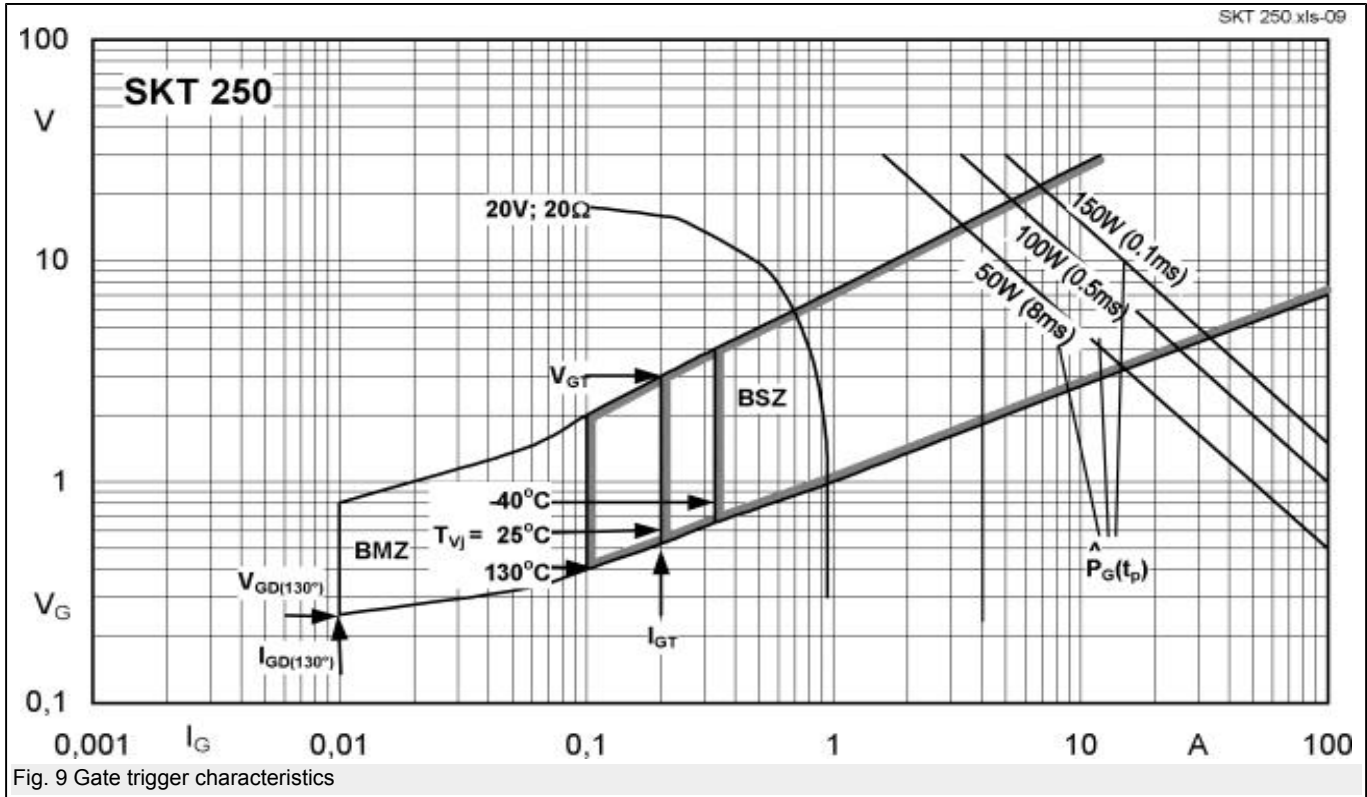
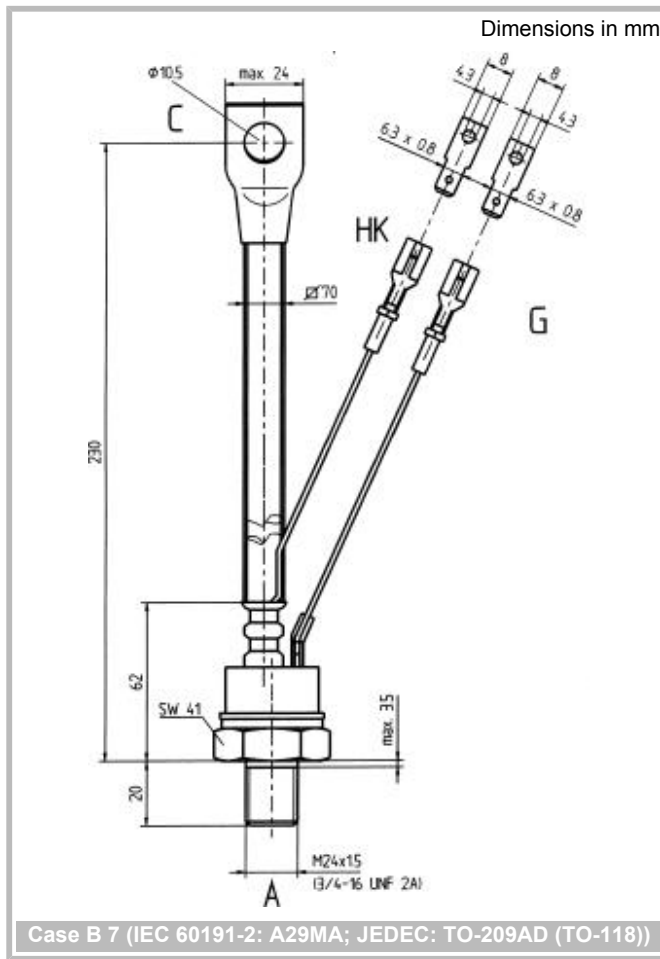


Fig. 9 Gate trigger characteristics

Cases / Circuits



This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.